

ABSTRACT

A semiconductor integrated circuit device (10) is composed of an LSI function unit (11) and a shield wiring layer (22) formed on the unit. The LSI function unit (11) includes
5 a semiconductor substrate (12) and a first insulating film (13), and the semiconductor substrate (12) is formed with a circuit element including, for example, a MOS transistor (14). The shield wiring layer (22) is composed of a lower shield line (23), a third insulating film (24), an upper shield line (25), and a fourth insulating film (26) sequentially stacked above a second insulating film (17). The directions in which the lower and upper
10 shield lines (23) and (25) are arranged intersect each other.